



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **HAYASHI, et al.**

Group Art Unit: **2813**

Serial No.: **09/955,600**

Examiner: **NGUYEN, Tuan H.**

Filed: **September 19, 2001**

Confirmation No.: **1668**

For: **SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME
AND METHOD OF FORMING NITRIDE BASED SEMICONDUCTOR LAYER**

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: December 30, 2003

Sir:

In response to the Office Action dated **August 1, 2003**, please amend the above-identified application as follows:

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TECHNOLOGY CENTER 2800